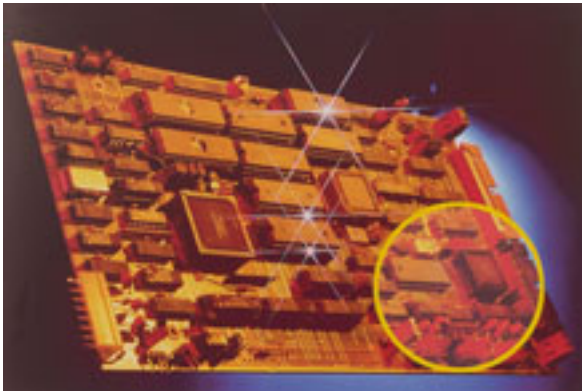


Process for Power Management Applications



PolarFab offers a 1.25-micron, 30 V junction-isolated modular bipolar process for 6 inches wafers. The BP30 process is ideal for power management applications up to 30 V including amplifiers, line drivers, and other linear applications. The PB30 process employs a lateral isolation technique that provides tight packing density without increasing process complexity. A washed emitter in the NPN transistor increases the performance of the chip by keeping the size of the NPN small, which reduces parasitics. The NPN transistor is capable of 3 GHz. The process also includes a 30 V lateral PNP transistor, a 30 V substrate vertical PNP transistor, two implanted resistors, a Schottky diode, a buried zener diode, and high density capacitors.

Source URL (retrieved on 01/25/2015 - 9:28am):

<http://www.wirelessdesignmag.com/product-releases/2002/12/process-power-management-applications>